



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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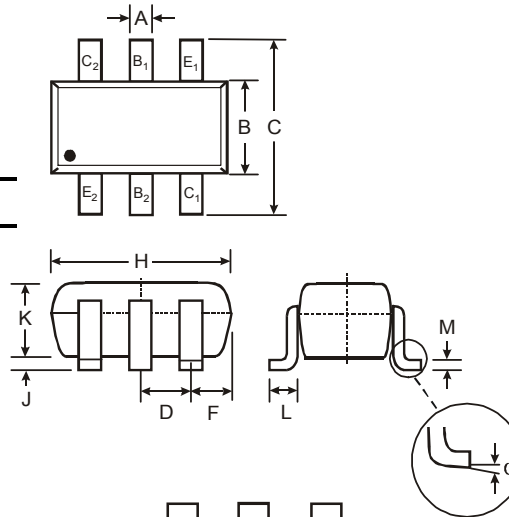


Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- One 500mA PNP and One 100mA NPN
- Lead Free/RoHS Compliant (Note 1)
- "Green" Device (Note 3 and 4)

Mechanical Data

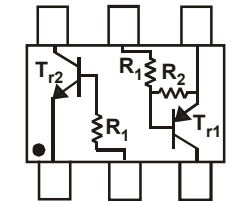
- Case: SOT-363
- Case Material - Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020A
- Terminals: Finish - Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Code: C73 See Page 4
- Ordering & Date Code: See Page 4
- Terminal Connections: See Diagram
- Weight: 0.015 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°

All Dimensions in mm

P/N	R1	R2
MIMD10A	Tr1 Tr2	0.1K 10K 10K -



SCHEMATIC DIAGRAM

Maximum Ratings PNP Section Tr1 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	-5 to +5	V
Output Current	I_O	-500	mA

Maximum Ratings NPN Section Tr2 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA

Maximum Ratings - Total @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 2)	P_d	200	mW
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics PNP Section Tr1 @_{T_A} = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	V _{I(off)}	-0.3	—	—	V	V _{CC} = -5V, I _O = -100μA
	V _{I(on)}	—	—	-1.5		V _O = 0.3, I _O = -100mA
Output Voltage	V _{O(on)}	—	-0.1	-0.3	V	I _O = -100mA/-5mA
Input Current	I _I	—	—	-25	mA	V _I = -2V
Output Current	I _{O(off)}	—	—	-0.5	μA	V _{CC} = -50V, V _I = 0V
DC Current Gain	G _I	68	—	—	—	—
Gain-Bandwidth Product*	f _T	—	200	—	MHz	V _{CE} = -10V, I _E = -50mA, f = 100MHz

* Transistor - For Reference Only

Electrical Characteristics NPN Section Tr2 @_{T_A} = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CB0}	50	—	—	V	I _C = 50μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	50	—	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5	—	—	V	I _E = 50μA
Collector Cutoff Current	I _{CB0}	—	—	0.5	μA	V _{CB} = 50V
Emitter Cutoff Current	I _{EBO}	—	—	0.5	μA	V _{EB} = 4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	0.3	V	I _C /I _B = 10mA / 1.0mA
DC Current Transfer Ratio	h _{FE}	100	250	600	—	I _C = 1mA, V _{CE} = 5V
Gain-Bandwidth Product*	f _T	—	250	—	MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz

* Transistor - For Reference Only

Typical Curves – Tr2

NEW PRODUCT

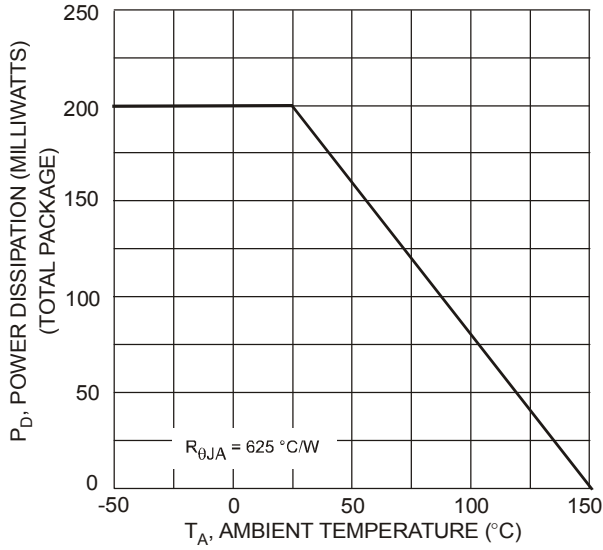


Fig. 1 Derating Curve

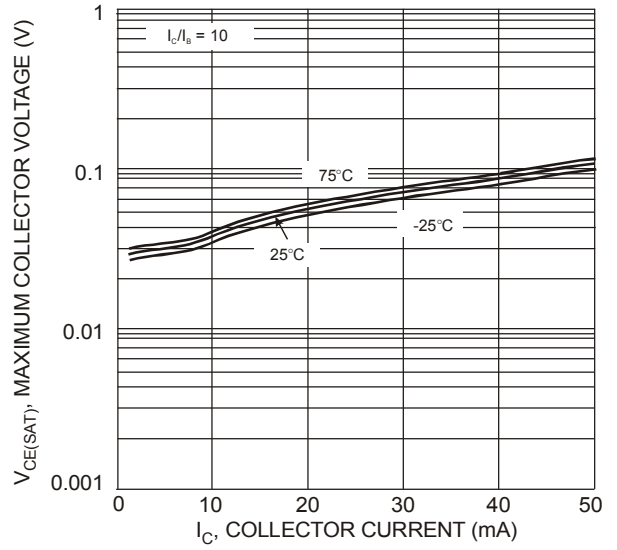


Fig. 2 V_{CE(SAT)} vs. I_C

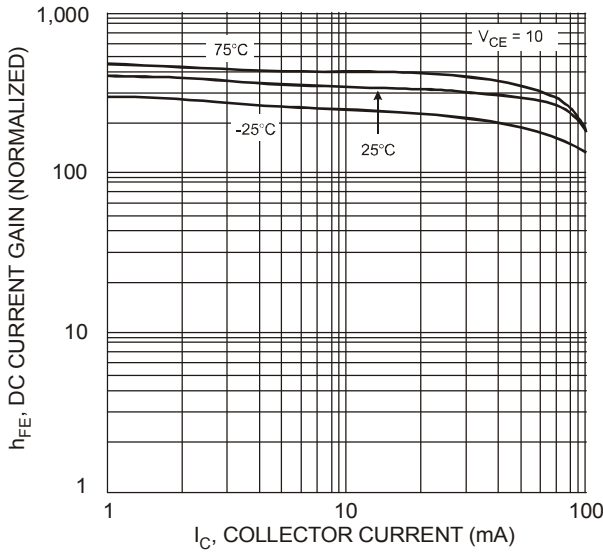


Fig. 3 DC Current Gain

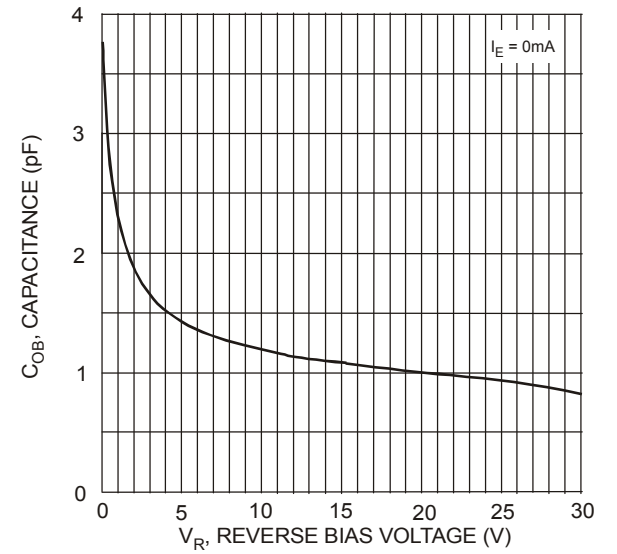


Fig. 4 Output Capacitance

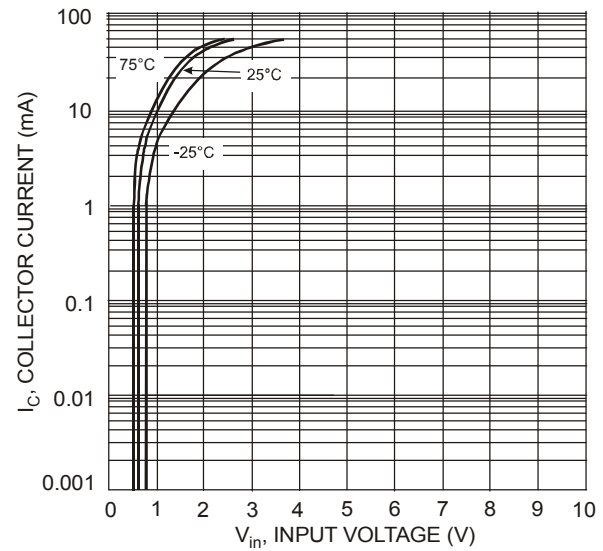


Fig. 5 Collector Current vs. Input Voltage

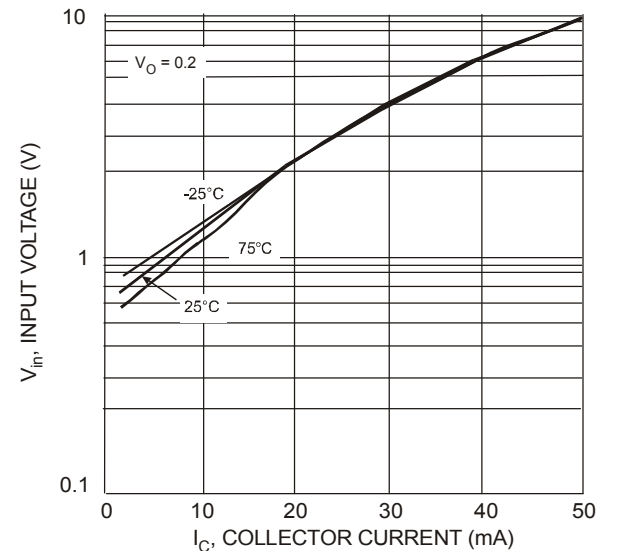


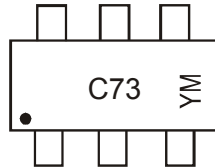
Fig. 6 Input Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
MIMD10A-7-F	SOT-363	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



C73 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: P = 2003
 M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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